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Titolo	On-Chip Electro-Static Discharge (ESD) Protection for Radio-Frequency Integrated Circuits // by Qiang Cui, Juin J. Liou, Jean-Jacques Hajjar, Javier Salcedo, Yuanzhong Zhou, Parthasarathy Srivatsan
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Nota di bibliografia	Includes bibliographical references.
Nota di contenuto	Basics in ESD Protection of Radio Frequency Integrated Circuits -- On-Chip Protection Solution for Radio Frequency Integrated Circuits in Standard CMOS Process -- Design of SiGe SCR devices for Radio Frequency Integrated Circuits in SiGe BiCMOS Process -- On-Chip Radio Frequency ESD Protection Solution in GaAs pHEMT Process -- Conclusion.
Sommario/riassunto	This book enables readers to design effective ESD protection solutions for all mainstream RF fabrication processes (GaAs pHEMT, SiGe HBT, CMOS). The new techniques introduced by the authors have much higher protection levels and much lower parasitic effects than those of existing ESD protection devices. The authors describe in detail the ESD phenomenon, as well as ESD protection fundamentals, standards, test equipment, and basic design strategies. Readers will benefit from realistic case studies of ESD protection for RFICs and will learn to increase significantly modern RFICs' ESD safety level, while maximizing RF performance. Describes in detail the ESD phenomenon, as well as

ESD protection fundamentals, standards, test equipment, and basic design strategies; Enables readers to design effective ESD protection solutions for all mainstream RF fabrication processes (GaAs pHEMT, SiGe HBT, CMOS); Includes realistic case studies of ESD protection for RFICs that resulted in significantly increased ESD safety level, while maximizing RF performance.
